

Day : Thursday
Date: 8/10/2006

Time: 05:40:45

PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = SAKURADA

First Name = MASAHIRO

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|--------------------------|-------------------------|--------|------------|---|--------------------|
| 08498894 | 5609682 | 150 | 07/06/1995 | A METHOD FOR THE PREPARATION OF SILICON SINGLE CRYSTAL | SAKURADA, MASAHIRO |
| 08565100 | 5667584 | 150 | 11/30/1995 | METHOD FOR THE PREPARATION OF A SINGLE CRYSTAL OF SILICON WITH DECREASED CRYSTAL DEFECTS | SAKURADA, MASAHIRO |
| 08655810 | 5817171 | 150 | 05/31/1996 | APPARATUS AND METHOD FOR PRODUCING SINGLE CRYSTAL USING CZOCHRALSKI TECHNIQUE | SAKURADA, MASAHIRO |
| 08660198 | 5728211 | 250 | 06/03/1996 | SILICON SINGLE CRYSTAL WITH LOW DEFECT DENSITY AND METHOD OF PRODUCING SAME | SAKURADA, MASAHIRO |
| 08666654 | 5704973 | 150 | 06/18/1996 | AN APPARATUS AND METHOD FOR THE UNIFORM DISTRIBUTION OF CRYSTAL DEFECTS UPON A SILICON SINGLE CRYSTAL | SAKURADA, MASAHIRO |
| 08768282 | 5730800 | 150 | 12/17/1996 | FUSED SILICA GLASS CRUCIBLE | SAKURADA, MASAHIRO |
| 08798472 | 5948163 | 250 | 02/10/1997 | APPARATUS FOR MANUFACTURING CRYSTALS ACCORDING TO THE CZOCHRALSKI METHOD, AND CRYSTALS MANUFACTURED BY THE MANUFACTURING METHOD | SAKURADA, MASAHIRO |
| 09090400 | 5938842 | 150 | 06/04/1998 | METHOD FOR PRODUCING A SINGLE CRYSTAL USING CZOCHRALSKI TECHNIQUE | SAKURADA, MASAHIRO |

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|-----------------|--|-----|------------|---|--------------------|
| <u>09125339</u> | <u>6071337</u> | 150 | 08/13/1998 | APPARATUS AND METHOD FOR PRODUCING CRYSTALS BY THE CZOCHRALSKI METHOD AND CRYSTALS PRODUCED BY THIS METHOD | SAKURADA, MASAHIRO |
| <u>09232561</u> | <u>6174364</u> | 150 | 01/15/1999 | METHOD FOR PRODUCING SILICON MONOCRYSTAL AND SILICON MONOCRYSTAL WAFER | SAKURADA, MASAHIRO |
| <u>09328278</u> | <u>6190452</u> | 150 | 06/08/1999 | SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING IT | SAKURADA, MASAHIRO |
| <u>09646713</u> | <u>6565822</u> | 150 | 09/21/2000 | EPITAXIAL SILICON WAFER, METHOD FOR PRODUCING THE SAME AND SUBSTRATE FOR EPITAXIAL SILICON WAFER | SAKURADA, MASAHIRO |
| <u>09727275</u> | <u>6482260</u> | 150 | 11/30/2000 | SILICON SINGLE CRYSTAL WAFER AND A METHOD FOR PRODUCING IT | SAKURADA, MASAHIRO |
| <u>10204935</u> | <u>6913646</u> | 150 | 08/27/2002 | SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING SILICON SINGLE CRYSTAL | SAKURADA, MASAHIRO |
| <u>10312921</u> | <u>6893499</u> | 150 | 12/26/2002 | SILICON SINGLE CRYSTAL WAFER AND METHOD FOR MANUFACTURING THE SAME | SAKURADA, MASAHIRO |
| <u>10500580</u> | Not Issued | 93 | 07/01/2004 | AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER | SAKURADA, MASAHIRO |
| <u>10512470</u> | Not Issued | 30 | 10/26/2004 | A SILICON SINGLE CRYSTAL WAFER, AN EPITAXIAL WAFER AND A METHOD FOR PRODUCING A SILICON SINGLE CRYSTAL | SAKURADA, MASAHIRO |
| <u>10516347</u> | Not Issued <i>Applicants Inventor</i> | 30 | 11/30/2004 | GRAPHITE HEATER FOR PRODUCING SINGLE CRYSTAL, APPARATUS FOR PRODUCING SINGLE CRYSTAL, AND METHOD FOR PRODUCING SINGLE CRYSTAL | SAKURADA, MASAHIRO |
| <u>10530557</u> | Not Issued | 20 | 04/07/2005 | Annealed wafer and method for manufacturing the same | SAKURADA, MASAHIRO |

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|--------------------------|------------|----|------------|--|--------------------|
| 10538878 | Not Issued | 41 | 06/14/2005 | Method of producing p-doped silicon single crystal and p-doped n-type silicon single crystal wafer | SAKURADA, MASAHIRO |
| 10542376 | Not Issued | 30 | 07/14/2005 | AN SOI WAFER AND A METHOD FOR PRODUCING THE SAME | SAKURADA, MASAHIRO |
| 10546693 | Not Issued | 25 | 08/22/2005 | An soi wafer and a method for producing the same | SAKURADA, MASAHIRO |
| 10560581 | Not Issued | 19 | 01/01/0001 | Method for producing a single crystal and a single crystal | SAKURADA, MASAHIRO |
| 10561205 | Not Issued | 25 | 02/03/2006 | Process for producing single crystal and single crystal | SAKURADA, MASAHIRO |
| 10561865 | Not Issued | 41 | 02/20/2006 | Method for producing single crystal and single crystal | SAKURADA, MASAHIRO |

Inventor Search Completed: No Records to Display.

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Day : Thursday
Date: 8/10/2006


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Time: 05:43:19

Inventor Name Search Result

Your Search was:

Last Name = FUSEGAWA

First Name = IZUMI

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|-----------------|------------|--------|------------|--|-----------------|
| <u>06941624</u> | Not Issued | 161 | 12/11/1986 | METHOD AND APPARATUS FOR CZOCHRALSKI SINGLE CRYSTAL GROWING | FUSEGAWA, IZUMI |
| <u>07242414</u> | 4956153 | 250 | 09/09/1988 | APPARATUS FOR CZOCHRALSKI SINGLE CRYSTAL GROWING | FUSEGAWA, IZUMI |
| <u>07496750</u> | 5110404 | 150 | 03/21/1990 | METHOD FOR HEAT PROCESSING OF SILICON | FUSEGAWA, IZUMI |
| <u>07703750</u> | Not Issued | 166 | 05/21/1991 | METHOD FOR PULLING UP SEMICONDUCTOR SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>07713848</u> | 5306387 | 150 | 06/12/1991 | METHOD FOR PULLING UP SEMICONDUCTOR SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>07729026</u> | Not Issued | 161 | 07/12/1991 | METHOD FOR PULLING SEMICONDUCTOR SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>07796385</u> | 5688319 | 150 | 11/22/1991 | METHOD FOR TESTING ELECTRICAL PROPERTIES OF SILICON SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>07850506</u> | 5262338 | 250 | 03/13/1992 | METHOD FOR FABRICATION OF SEMICONDUCTOR DEVICE | FUSEGAWA, IZUMI |
| <u>07850915</u> | Not Issued | 166 | 03/13/1992 | HEAT TREATMENT OF SI SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>07850916</u> | 5386796 | 150 | 03/13/1992 | METHOD FOR TESTING QUALITY OF SILICON WAFER | FUSEGAWA, IZUMI |
| <u>07852612</u> | 5248378 | 150 | 03/17/1992 | METHOD AND APPARATUS FOR PRODUCING SILICON SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>07953918</u> | 5359959 | 150 | 09/30/1992 | METHOD FOR PULLING UP | FUSEGAWA, IZUMI |

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|-----------------|----------------|-----|------------|--|-----------------|
| | | | | SEMI-CONDUCTOR SINGLE CRYSTAL | |
| <u>07961182</u> | <u>5462010</u> | 250 | 10/14/1992 | APPARATUS FOR SUPPLYING GRANULAR RAW MATERIAL FOR A SEMICONDUCTOR SINGLE CRYSTAL PULLING APPARATUS | FUSEGAWA, IZUMI |
| <u>07961764</u> | <u>5373805</u> | 250 | 10/15/1992 | SINGLE CRYSTAL PULLING APPARATUS | FUSEGAWA, IZUMI |
| <u>08011744</u> | <u>5340434</u> | 250 | 02/01/1993 | PROCESS FOR PRODUCING SILICON SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>08012172</u> | <u>5361721</u> | 250 | 02/02/1993 | SINGLE CRYSTAL PULLING APPARATUS | FUSEGAWA, IZUMI |
| <u>08108285</u> | Not Issued | 166 | 08/19/1993 | HEAT TREATMENT OF SI SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>08190604</u> | Not Issued | 166 | 02/02/1994 | CRUCIBLE FOR PULLING SILICON SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>08238722</u> | <u>5534112</u> | 150 | 05/05/1994 | METHOD FOR TESTING ELECTRICAL PROPERTIES OF SILICON SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>08293214</u> | Not Issued | 166 | 08/19/1994 | APPARATUS FOR PRODUCING SILICON SINGLE CRYSTAL GROWN BY CZOCHRALSKI METHOD | FUSEGAWA, IZUMI |
| <u>08395837</u> | <u>5501172</u> | 150 | 02/28/1995 | METHOD OF GROWING SILICON SINGLE CRYSTALS | FUSEGAWA, IZUMI |
| <u>08445029</u> | Not Issued | 166 | 05/19/1995 | HEAT TREATMENT OF SI SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>08510436</u> | <u>5720809</u> | 250 | 08/02/1995 | CRUCIBLE FOR PULLING SILICON SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>08552164</u> | Not Issued | 166 | 11/02/1995 | APPARATUS FOR PRODUCING SILICON SINGLE CRYSTAL GROWN BY CZOCHRALSKI METHOD | FUSEGAWA, IZUMI |
| <u>08699719</u> | <u>5725661</u> | 250 | 07/01/1996 | EQUIPMENT FOR PRODUCING SILICON SINGLE CRYSTALS | FUSEGAWA, IZUMI |
| <u>08754784</u> | <u>5938841</u> | 150 | 11/21/1996 | DEVICE FOR PRODUCING SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>08760959</u> | <u>5766346</u> | 150 | 12/05/1996 | APPARATUS FOR PRODUCING SILICON SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>08770499</u> | <u>5851283</u> | 150 | 12/20/1996 | METHOD AND APPARATUS | FUSEGAWA, IZUMI |

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|-----------------|----------------|-----|------------|---|-----------------|
| | | | | FOR PRODUCTION OF SINGLE CRYSTAL | |
| <u>08773351</u> | <u>5871583</u> | 150 | 12/26/1996 | AN APPARATUS FOR PRODUCING SILICON CRYSTAL | FUSEGAWA, IZUMI |
| <u>08916291</u> | <u>5834322</u> | 250 | 08/22/1997 | HEAT TREATMENT OF SI SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>09270277</u> | <u>6153009</u> | 150 | 03/16/1999 | METHOD FOR PRODUCING A SILICON SINGLE CRYSTAL AND THE SILICON SINGLE CRYSTAL PRODUCED THEREBY | FUSEGAWA, IZUMI |
| <u>09290261</u> | <u>6117231</u> | 150 | 04/13/1999 | METHOD OF MANUFACTURING SEMICONDUCTOR SILICON SINGLE CRYSTAL WAFER | FUSEGAWA, IZUMI |
| <u>09429343</u> | <u>6387466</u> | 150 | 10/28/1999 | SINGLE-CRYSTAL SILICON WAFER | FUSEGAWA, IZUMI |
| <u>09646713</u> | <u>6565822</u> | 150 | 09/21/2000 | EPITAXIAL SILICON WAFER, METHOD FOR PRODUCING THE SAME AND SUBSTRATE FOR EPITAXIAL SILICON WAFER | FUSEGAWA, IZUMI |
| <u>09673480</u> | Not Issued | 161 | 10/16/2000 | Method for producing silicon single crystals | FUSEGAWA, IZUMI |
| <u>09674858</u> | <u>6423285</u> | 150 | 11/07/2000 | Method for producing silicon single crystal and production apparatus therefor as well as crystal and silicon wafer produced by the method | FUSEGAWA, IZUMI |
| <u>09937132</u> | <u>6632280</u> | 150 | 09/21/2001 | SINGLE CRYSTAL GROWING DEVICE | FUSEGAWA, IZUMI |
| <u>09959381</u> | <u>6592662</u> | 150 | 10/24/2001 | METHOD FOR PREPARING SILICON SINGLE CRYSTAL AND SILICON SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>09979519</u> | <u>6632411</u> | 150 | 11/23/2001 | SILICON WAFER AND METHOD FOR PRODUCING SILICON SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>10204278</u> | <u>6764548</u> | 150 | 08/20/2002 | APPARATUS AND METHOD FOR PRODUCING SILICON SEMICONDUCTOR SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>10204935</u> | <u>6913646</u> | 150 | 08/27/2002 | SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING SILICON | FUSEGAWA, IZUMI |

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|-----------------|---------------------------------------|-----|------------|---|-----------------|
| | | | | SINGLE CRYSTAL | |
| <u>10312921</u> | 6893499 | 150 | 12/26/2002 | SILICON SINGLE CRYSTAL WAFER AND METHOD FOR MANUFACTURING THE SAME | FUSEGAWA, IZUMI |
| <u>10500580</u> | Not Issued | 93 | 07/01/2004 | AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER | FUSEGAWA, IZUMI |
| <u>10510695</u> | Not Issued | 41 | 10/08/2004 | METHOD OF MANUFACTURING SILICON SINGLE CRYSTAL, SILICON SINGLE CRYSTAL AND SILICON WAFER | FUSEGAWA, IZUMI |
| <u>10512470</u> | Not Issued | 30 | 10/26/2004 | A SILICON SINGLE CRYSTAL WAFER, AN EPITAXIAL WAFER AND A METHOD FOR PRODUCING A SILICON SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>10516347</u> | Not Issued <i>App. Inventor</i> | 30 | 11/30/2004 | GRAPHITE HEATER FOR PRODUCING SINGLE CRYSTAL, APPARATUS FOR PRODUCING SINGLE CRYSTAL, AND METHOD FOR PRODUCING SINGLE CRYSTAL | FUSEGAWA, IZUMI |
| <u>10538878</u> | Not Issued | 41 | 06/14/2005 | Method of producing p-doped silicon single crystal and p-doped n-type silicon single crystal wafer | FUSEGAWA, IZUMI |
| <u>10542376</u> | Not Issued | 30 | 07/14/2005 | AN SOI WAFER AND A METHOD FOR PRODUCING THE SAME | FUSEGAWA, IZUMI |
| <u>10561865</u> | Not Issued | 41 | 02/20/2006 | Method for producing single crystal and single crystal | FUSEGAWA, IZUMI |
| <u>10568186</u> | Not Issued | 20 | 03/03/2006 | Process for producing single crystal and silicon crystal wafer | FUSEGAWA, IZUMI |

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 **PALM INTRANET****Inventor Name Search Result**

Your Search was:

Last Name = SOETA

First Name = SATOSHI

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|--------------------------|---|--------|------------|---|----------------|
| 08759223 | 5888298 | 150 | 12/05/1996 | MEMBER-HANDLING MECHANISM, AND MEMBER-HANDLING JIG FOR A CRYSTAL PULLING APPARATUS | SOETA, SATOSHI |
| 08776776 | 5972106 | 150 | 02/10/1997 | DEVICE AND METHOD FOR PRODUCING SINGLE CRYSTAL | SOETA, SATOSHI |
| 08804146 | 5851287 | 150 | 02/20/1997 | SEED CRYSTAL HOLDER | SOETA, SATOSHI |
| 09508695 | 6280522 | 150 | 03/29/2000 | QUARTZ GLASS CRUCIBLE FOR PULLING SILICON SINGLE CRYSTAL AND PRODUCTION PROCESS FOR SUCH CRUCIBLE | SOETA, SATOSHI |
| 10516347 | Not Issued <i>App'l. exists' Invention</i> | 30 | 11/30/2004 | GRAPHITE HEATER FOR PRODUCING SINGLE CRYSTAL, APPARATUS FOR PRODUCING SINGLE CRYSTAL, AND METHOD FOR PRODUCING SINGLE CRYSTAL | SOETA, SATOSHI |

Inventor Search Completed: No Records to Display.

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PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = IIDA

First Name = MAKOTO

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|-----------------|----------------|--------|------------|---|---------------|
| <u>05810759</u> | <u>4163215</u> | 150 | 06/28/1977 | SAFETY LOCK SYSTEM | IIDA, MAKOTO |
| <u>05895605</u> | <u>4227577</u> | 150 | 04/12/1978 | FIRE-EXTINGUISHING SYSTEM | IIDA, MAKOTO |
| <u>06336323</u> | <u>4409341</u> | 150 | 12/31/1981 | COMPOSITION FOR FIRE RETARDANT URETHANE FOAM | IIDA, MAKOTO |
| <u>06880012</u> | <u>4734448</u> | 150 | 06/30/1986 | PROPYLENE POLYMER COMPOSITION | IIDA, MAKOTO |
| <u>07219267</u> | Not Issued | 166 | 07/15/1988 | ELECTROCONDUCTIVE RESIN COMPOSITION FOR MOLDING AND ELECTROMAGNETIC WAVE INTERFERENCE SHIELD STRUCTURE MOLDED FROM THE COMPOSITION | IIDA, MAKOTO |
| <u>07538113</u> | <u>5071223</u> | 150 | 06/14/1990 | CIRCUIT STRUCTURE FORMED BY INSERT MOLDING OF ELECTRIC AND/OR OPTICAL TRANSMISSION MEDIUM | IIDA, MAKOTO |
| <u>07592545</u> | Not Issued | 166 | 10/02/1990 | FOCUS DRAW-IN METHOD FOR OPTICAL DISC DEVICE | IIDA, MAKOTO |
| <u>07769348</u> | <u>6156427</u> | 250 | 10/02/1991 | ELECTROCONDUCTIVE RESIN COMPOSITION FOR MOLDING AND ELECTROMAGNETIC WAVE INTERFERENCE SHIELD STRUCTURE MOLDED FROM THE COMPOSITION | IIDA, MAKOTO |
| <u>07785000</u> | <u>5179601</u> | 150 | 10/30/1991 | METHOD OF MANUFACTURING CIRCUIT STRUCTURE BY INSERT MOLDING OF ELECTRIC AND/OR OPTICAL TRANSMISSION MEDIUM | IIDA, MAKOTO |
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|-----------------|----------------|-----|------------|--|--------------|
| <u>07866166</u> | Not Issued | 166 | 06/29/1992 | OPTICAL DISK SYSTEM | IIDA, MAKOTO |
| <u>07939045</u> | Not Issued | 166 | 09/03/1992 | FOCUS DRAW-IN SYSTEM FOR OPTICAL DISC DEVICE | IIDA, MAKOTO |
| <u>08137211</u> | <u>5414682</u> | 150 | 10/18/1993 | FOCUS DRAW-IN SYSTEM FOR OPTICAL DISC DEVICE | IIDA, MAKOTO |
| <u>08172413</u> | <u>5491301</u> | 150 | 12/22/1993 | SHIELDING METHOD AND CIRCUIT BOARD EMPLOYING THE SAME | IIDA, MAKOTO |
| <u>08279318</u> | <u>5461599</u> | 150 | 07/22/1994 | OPTICAL DISK SYSTEM | IIDA, MAKOTO |
| <u>08809295</u> | Not Issued | 161 | 03/27/1997 | PROPYLENE RESIN COMPOSITION FOR AUTOMOTIVE INTERIOR PARTS, AND AUTOMOTIVE INTERIOR PARTS | IIDA, MAKOTO |
| <u>08827060</u> | Not Issued | 161 | 03/26/1997 | PRESS WORKING METHOD AND EQUIPMENT THEREFOR | IIDA, MAKOTO |
| <u>08915397</u> | <u>5871578</u> | 150 | 08/20/1997 | METHODS FOR HOLDING AND PULLING SINGLE CRYSTAL | IIDA, MAKOTO |
| <u>08923963</u> | <u>5911821</u> | 150 | 09/05/1997 | METHOD OF HOLDING A MONOCRYSTAL, AND METHOD OF GROWING THE SAME | IIDA, MAKOTO |
| <u>08929670</u> | <u>5964941</u> | 150 | 09/15/1997 | CRYSTAL PULLING METHOD AND APPARATUS | IIDA, MAKOTO |
| <u>08944869</u> | <u>5882397</u> | 150 | 10/06/1997 | CRYSTAL PULLING METHOD | IIDA, MAKOTO |
| <u>09039830</u> | <u>6053975</u> | 150 | 03/16/1998 | CRYSTAL HOLDING APPARATUS | IIDA, MAKOTO |
| <u>09101941</u> | <u>6120749</u> | 150 | 07/17/1998 | SILICON SINGLE CRYSTAL WITH NO CRYSTAL DEFECT IN PERIPHERAL PART OF WAFER AND PROCESS FOR PRODUCING THE SAME | IIDA, MAKOTO |
| <u>09109530</u> | <u>5968264</u> | 150 | 07/02/1998 | METHOD AND APPARATUS FOR MANUFACTURING A SILICON SINGLE CRYSTAL HAVING FEW CRYSTAL DEFECTS, AND A SILICON SINGLE CRYSTAL AND SILICON WAFERS MANUFACTURED BY THE SAME | IIDA, MAKOTO |
| <u>09140288</u> | <u>5948164</u> | 250 | 08/25/1998 | SEED CRYSTAL HOLDER | IIDA, MAKOTO |

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|-----------------|----------------|-----|------------|--|--------------|
| <u>09173931</u> | <u>6027562</u> | 150 | 10/16/1998 | METHOD FOR PRODUCING A SILICON SINGLE CRYSTAL HAVING FEW CRYSTAL DEFECTS, AND A SILICON SINGLE CRYSTAL AND SILICON WAFERS PRODUCED BY THE METHOD | IIDA, MAKOTO |
| <u>09188490</u> | <u>6066306</u> | 150 | 11/09/1998 | SILICON SINGLE CRYSTAL WAFER HAVING FEW CRYSTAL DEFECTS, AND METHOD FOR PRODUCING THE SAME | IIDA, MAKOTO |
| <u>09194232</u> | <u>6445872</u> | 150 | 11/23/1998 | RECORDING AND REPRODUCING APPARATUS FOR RECORDING DIGITAL BROADCAST COMPRESSION-CODED DATA T OF VIDEO SIGNALS OF A MULTIPLICITY OF CHANNELS | IIDA, MAKOTO |
| <u>09197130</u> | <u>6048395</u> | 150 | 11/20/1998 | METHOD FOR PRODUCING A SILICON SINGLE CRYSTAL HAVING FEW CRYSTAL DEFECTS | IIDA, MAKOTO |
| <u>09264514</u> | <u>6191009</u> | 150 | 03/08/1999 | METHOD FOR PRODUCING SILICON SINGLE CRYSTAL WAFER AND SILICON SINGLE CRYSTAL WAFER | IIDA, MAKOTO |
| <u>09294323</u> | <u>6191675</u> | 150 | 04/20/1999 | HIGH VOLTAGE TRANSFORMER AND IGNITION TRANSFORMER USING THE SAME | IIDA, MAKOTO |
| <u>09313856</u> | <u>6299982</u> | 150 | 05/18/1999 | SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING SILICON SINGLE CRYSTAL WAFER | IIDA, MAKOTO |
| <u>09318055</u> | <u>6077343</u> | 150 | 05/25/1999 | SILICON SINGLE CRYSTAL WAFER HAVING FEW DEFECTS WHEREIN NITROGEN IS DOPED AND A METHOD FOR PRODUCING IT | IIDA, MAKOTO |
| <u>09329615</u> | <u>6197109</u> | 150 | 06/10/1999 | METHOD FOR PRODUCING LOW DEFECT SILICON SINGLE CRYSTAL DOPED WITH NITROGEN | IIDA, MAKOTO |
| <u>09359078</u> | <u>6159438</u> | 150 | 07/22/1999 | METHOD AND APPARATUS FOR MANUFACTURING A | IIDA, MAKOTO |

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|-----------------|----------------|-----|------------|--|--------------|
| | | | | SILICON SINGLE CRYSTAL HAVING FEW CRYSTAL DEFECTS, AND A SILICON SINGLE CRYSTAL AND SILICON WAFERS MANUFACTURED BY THE SAME | |
| <u>09454841</u> | <u>6120599</u> | 150 | 12/06/1999 | SILICON SINGLE CRYSTAL WAFER HAVING FEW CRYSTAL DEFECTS, AND METHOD FOR PRODUCING THE SAME | IIDA, MAKOTO |
| <u>09459849</u> | <u>6120598</u> | 150 | 12/13/1999 | METHOD FOR PRODUCING A SILICON SINGLE CRYSTAL HAVING FEW CRYSTAL DEFECTS, AND A SILICON SINGLE CRYSTAL AND SILICON WAFERS PRODUCED BY THE METHOD | IIDA, MAKOTO |
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